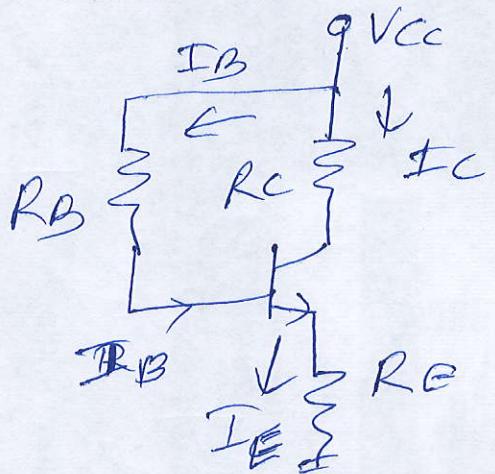


(3) Emitter Feedback Bias / Base Bias
WITH Emitter Feedback / Emitter
Resistor Biasing

It is a modification of fixed bias circuit (method no. 1). It uses an additional resistor R_E which is connected in the emitter. It has 3 resistors R_B , R_C & R_E .

Analysis:

Determination of Q point.

(i) Input section:

$$V_{CC} = I_B R_B + V_{BE} + I_E R_E$$

$$\left[\text{put } I_E R_E = (\beta + 1) I_B R_E \right]$$

$$\begin{aligned} I_E &= I_C + I_B \\ &= \beta I_B + I_B = (\beta + 1) I_B \end{aligned}$$

$$\therefore V_{CC} = I_B R_B + V_{BE} + (\beta + 1) I_B R_E$$

$$I_B \approx [R_B + (\beta + 1) R_E] = V_{CC} - V_{BE}$$

$$\therefore I_B = \frac{V_{CC} - V_{BE}}{R_B + (\beta + 1) R_E} \approx \frac{V_{CC}}{R_B + (\beta + 1) R_E}$$

$$\approx \frac{V_{CC}}{R_B + \beta R_E}$$

Assuming B771 & $V_{BE} \ll V_{CC}$.

$$I_C = B I_B = \frac{B V_{CC}}{R_B + R_E} = \frac{V_{CC}}{\frac{R_B + R_E}{B}} \quad \textcircled{1}$$

(ii) Output section.

$$V_{CC} = I_C R_C + V_{CE} + I_E R_E$$

$$\therefore V_{CE} = V_{CC} - (R_C + R_E) I_C$$

as $I_C \approx I_E$ - \textcircled{2}

Derivation of equation showing the effect of feedback.

$$V_{CC} = R_B I_B + V_{BE} + I_E R_E$$

$$\therefore I_B = \frac{V_{CC} - I_E R_E - V_{BE}}{R_B}$$

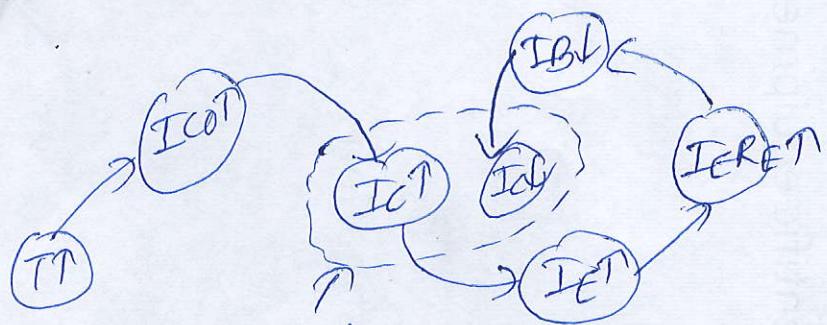
If V_{BE} is neglected then

$$I_B = \frac{V_{CC} - I_E R_E}{R_B} \quad \therefore \textcircled{3}$$

Suitability as biasing circuit

(1) Effect of temperature.

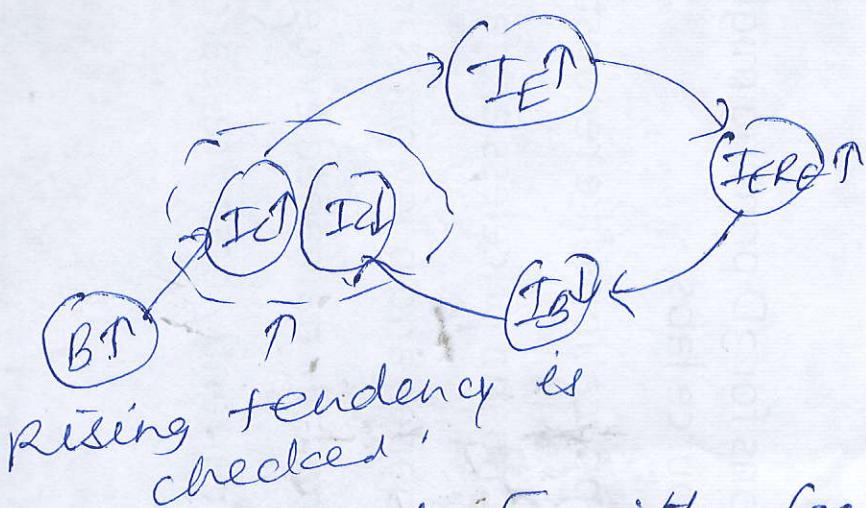
As the temperature increases I_{CO} increases
 $\therefore I_C$ increases and I_E increases $\therefore I_E R_E$
increases. This reduces $V_{CC} - I_E R_E$. $\therefore I_B$
reduces which results in reduction of I_C .
 I_C is not allowed to increase to the extent
it would have been in absence of R_E .
(Refer equation \textcircled{3})



Rising tendency
is checked.

- ② Transistor replaced by another transistor of same type having different value of B :

This circuit provides stabilization of Q point. If B increases then I_C of Q point also increases. $\therefore I_E$ also increases. $\therefore I_EFET$ increases. $\therefore I_B$ decreases and hence I_C decreases.



Rising tendency is checked.

Drawback of Emitter feedback bias circuit

The resistor R_E is present at the output side as well as the input side of the circuit. A feedback occurs through this resistor. The feedback voltage is proportional to I_E . Hence this circuit is also called current feedback biasing circuit.

While d.c. feedback helps in the stabilization of Q point, the a.c. feedback reduces the voltage gain of the amplifier.

This drawback can be remedied by putting a capacitor C_E across the resistor R_E . The capacitor C_E offers very low impedance to the a.c. current. The E is effectively placed at ground potential for the a.c. signal. The circuit now provides d.c. feedback for stabilization of Q point but does not give any a.c. feedback. The amplification of ac signal remains unaffected.

Stability factor

$$V_{CC} = I_B R_B + V_{BE} + I_E R_E$$

$$\text{putting } I_E = I_C + I_B$$

$$V_{CC} = I_B R_B + V_{BE} + (I_C + I_B) R_E$$

$$V_{CC} = I_B (R_B + R_E) + V_{BE} + I_C R_E$$

$$\therefore I_B (R_B + R_E) = V_{CC} - V_{BE} - I_C R_E$$

$$\therefore F_B = \frac{V_{CC} - V_{BE}}{R_B + R_E} - I_C \frac{R_E}{R_E + R_B}$$

Differentiating w.r.t. I_C .

$$\frac{dI_B}{dI_C} = -\frac{R_E}{R_E + R_B}$$

$$\therefore S = \frac{1+B}{1-B \frac{dI_B}{dI_C}} = \frac{1+B}{1-B \times -\frac{R_E}{R_E + R_B}} = \frac{1+B}{1+\frac{B R_E}{R_E + R_B}}$$

Why this circuit is not used.

(5)

The denominator in the equation

$$I_C = \frac{V_{CC}}{R_B + R_E}$$

can be independent of B

only if $R_E \gg \frac{R_B}{B}$.

This means that either R_E should be very high or R_B be very low.

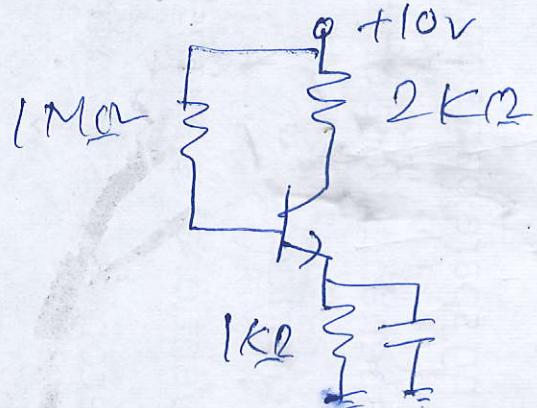
(i) High value of R_E

It will cause a large voltage drop across it. To obtain a particular operating point under this condition it will require a high d.c. source V_{CC} .

(ii) Low value of R_B - requires a separate low voltage supply in the circuit. Both the alternatives are impractical.

(i) Solved problems.

Calculate the values of I_B , I_C & I_E



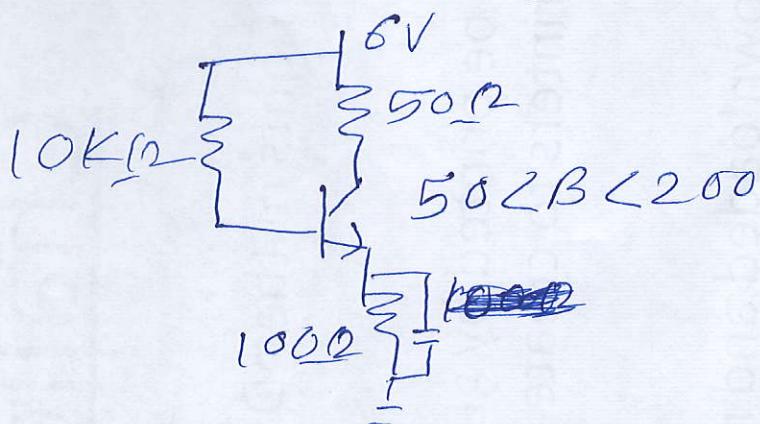
$$I_B = \frac{V_{CE}}{R_B + B R_E} = \frac{10}{1 \times 10^6 + 100 \times 1 \times 10^3}$$

$$= 9.09 \mu A$$

$$I_C = \beta I_B = 100 \times 9.09 \times 10^{-6} = 0.909 \text{ mA} \quad (6)$$

$$I_E = I_C + I_B = 9.09 \text{ mA} + 0.909 \text{ mA} \\ \approx 0.909 \text{ mA}$$

(2) Calculate the minimum and maximum value of I_E for the biasing circuit. Also calculate the corresponding value of V_{CE} . Germanium transistor is used (means $V_{BE} = 0.3 \text{ V}$)



$$I_B = \frac{V_{CC} - V_{BE}}{R_B + R_{RE}}$$

Multiply both sides by $\beta + 1$

$$\therefore (\beta + 1) I_B = \frac{V_{CC} - V_{BE}}{R_B + R_{RE}} (\beta + 1)$$

$$I_E = \frac{V_{CC} - V_{BE}}{R_B + R_{RE}} (\beta + 1)$$

(a) $\beta = 50$

$$I_E = \frac{(6 - 0.3)(50 + 1)}{10 \times 10^3 + 50 \times 100} \\ = 19.38 \text{ mA}$$

$$V_{CE} = V_{CC} - (R_C + R_E) I_E$$

(7)

$$= 6 - (100 + 50) \times 9.38 \times 10^{-3}$$

$$= 3.09 \text{ V}$$

(b) $B = 200$

$$I_E = \frac{(6-0.3)(200+1)}{10 \times 10^3 + 200 \times 100}$$

$$= 38.19 \text{ mA}$$

$$V_{CE} = 6 - (50 + 100) \times 38.19 \times 10^{-3}$$

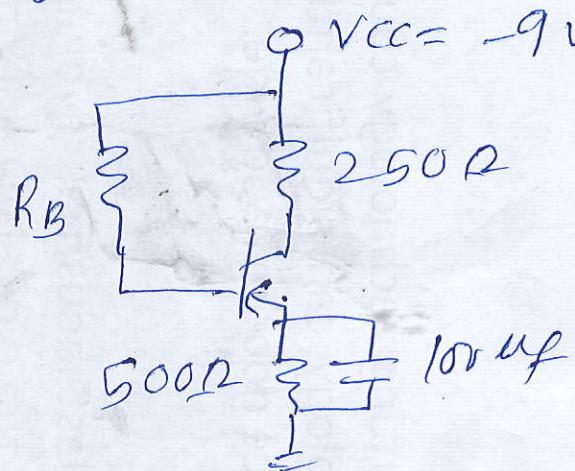
$$= 8.27 \text{ V}$$

[Conclusion (i) When β becomes 4 times

I_E becomes almost double.

(ii) When β changes from 50 to 200, operating point shifts very near saturation point.

(3) Calculate the value of R_B in the biasing circuit so that the Q point is fixed at $I_C = 8 \text{ mA}$, $V_{CE} = 3 \text{ V}$.



$$I_B R_B + I_E R_E = V_{CC} - V_{BE}$$

$$\therefore I_B R_B + (\beta + 1) I_B R_E = V_{CC} - V_{BE}$$

V_{BE} is neglected

$$\therefore I_B R_B = V_{CC} - (\beta + 1) I_B R_E \quad (8)$$

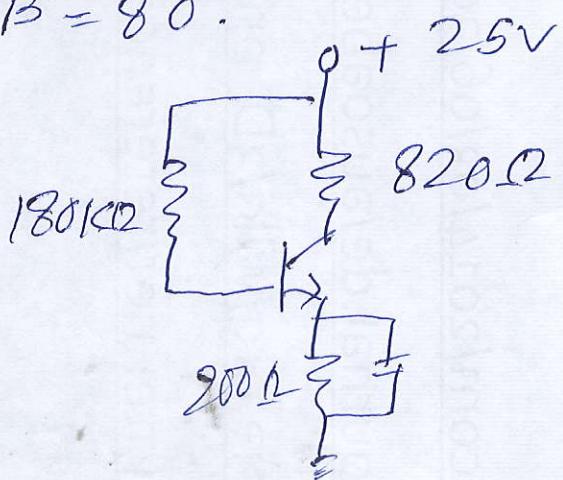
$$\therefore R_B = \frac{V_{CC} - (\beta + 1) I_B R_E}{I_B}$$

$$\text{Now } I_B = \frac{I_C}{\beta} = \frac{8 \times 10^{-3}}{80} = 100 \mu A.$$

$$\therefore R_B = \frac{9 - (80+1) \times 100 \times 10^{-6} \times 500}{100 \times 10^{-6}} \\ = 49.5 \text{ k}\Omega.$$

Assignment Problems.

(1) Determine the values of I_C , V_{CE} and stability factor. Given $V_{BE} = 0.7V$ and $\beta = 80$.



~~$V_{BE} = V_{CC} - V_{BE}$~~ draw circuits for (2) & (3).

(2) Calculate Q point. Neglect V_{BE} . Given $V_{CC} = 20V$, $R_B = 400 \text{ k}\Omega$, $R_C = 2 \text{ k}\Omega$, $R_E = 1 \text{ k}\Omega$ & $\beta = 100$

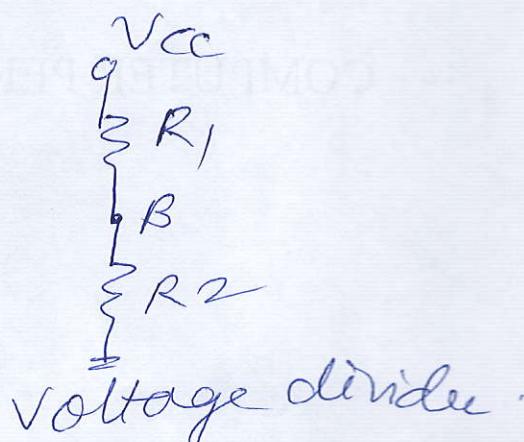
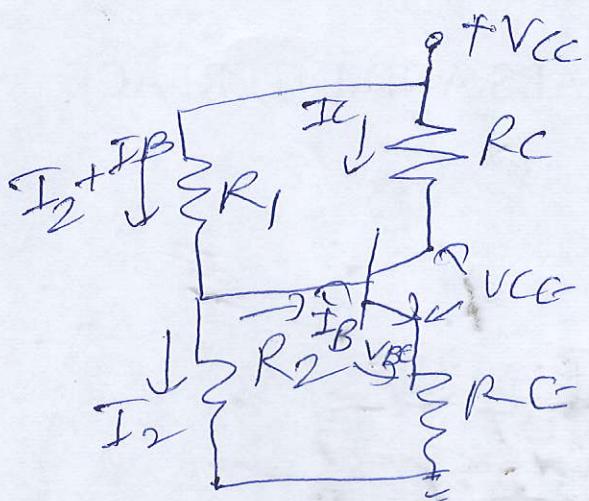
(3) Calculate Q point. Given $V_{BE} = 0.25V$. Given $V_{CE} = 10V$, $R_B = 75 \text{ k}\Omega$, $\beta = 80$, $R_C = 0.5 \text{ k}\Omega$, $R_E = 470 \text{ }\Omega$

(4). VOLTAGE DIVIDER BIAS / SELF BIAS. (a)

In all previous circuits I_C & V_{CE} depend upon B of the transistor. B is temperature sensitive especially for Si transistors therefore this circuit is designed which is independent of B . It is most widely used method.

Here R_1 & R_2 are connected across the supply voltage V_{CC} to provide biasing. R_E provides stabilisation. The name 'voltage divider' comes from the voltage divider formed by R_1 & R_2 .

The voltage drop across R_2 forward biases the B-E junction.

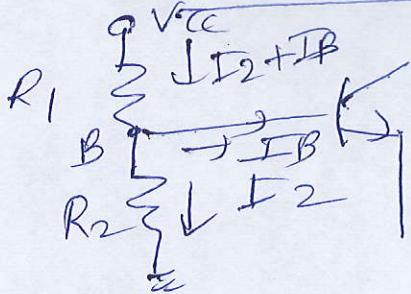


We will be studying analysis for the voltage-divider bias circuit

Q APPROXIMATE ANALYSIS

(10)

(a) Base circuit



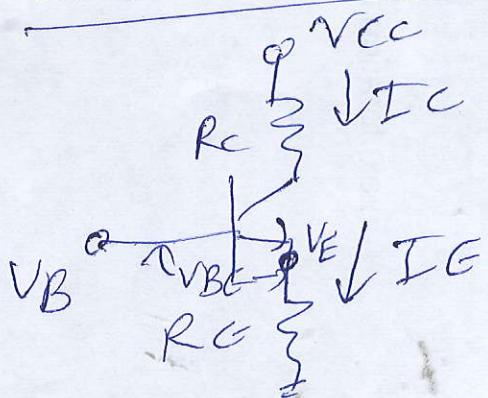
voltage across R_2 is the B voltage V_B

$$\therefore V_B = \frac{R_2}{R_1 (I_2 + I_B) + R_2 I_2} \times V_{CC}$$

as $I_2 \gg I_B$

$$V_B = \frac{R_2}{R_1 + R_2} \times V_{CC}$$

(b) Collector circuit



$$V_E = I_E R_E = V_B - V_{BE}$$

$$\therefore I_E = \frac{V_B - V_{BE}}{R_E}$$

$V_{BE} \ll V_B$

$$\therefore I_E = \frac{V_B}{R_E}$$

Applying KVL to the C circuit

$$V_{CC} = I_C R_C - V_{CE} - I_E R_E$$

$$\therefore V_{CE} = V_{CC} - I_C R_C - I_E R_E$$

As $I_C \approx I_E$.

$$V_{CE} = V_{CC} - (R_C + R_E) I_C \quad (1)$$

In the above analysis β does not appear which means that Q point does not depend upon the β .

Stabilization:

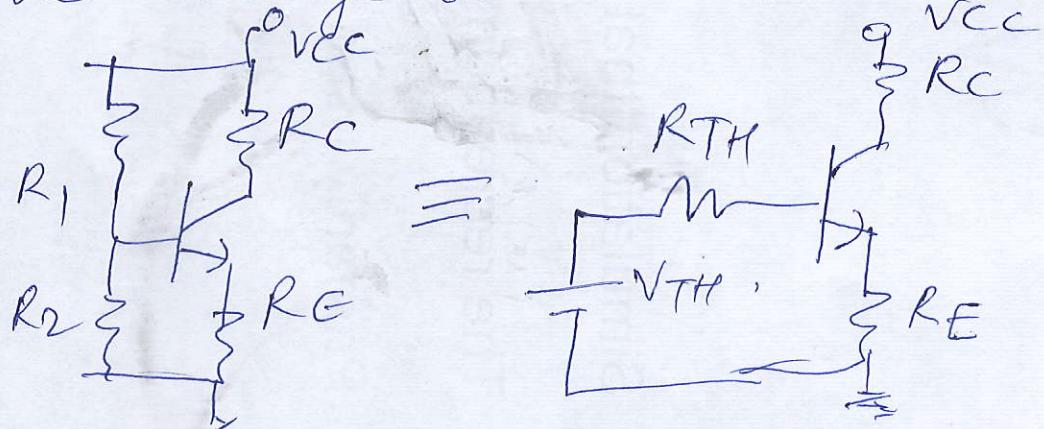
In this circuit excellent stabilization is provided by R_E .

$$V_{IB} = V_{BE} + I_E R_E$$

Suppose I_C increases due to rise in temperature. This will cause the voltage drop across ~~R_E~~ i.e. ~~R_E~~ to increase. As V_B is independent of I_C therefore V_{BE} decreases. This in turn causes I_B to decrease. $\therefore I_C$ will decrease.

(ii) ACCURATE ANALYSIS / EXACT ANALYSIS

Let us apply Thevenin's theorem to the voltage divider circuit



(12)

~~(a) Input section~~

$$V_{TH} = \frac{R_2}{R_1 + R_2} \times V_{CC}$$

$$R_{TH} = \frac{R_1 R_2}{R_1 + R_2}$$

(a) Input section:

$$V_{TH} = I_B R_{TH} + V_{BE} + I_E R_E$$

$$\text{putting } I_E = (\beta + 1) I_B$$

$$\therefore V_{TH} = I_B R_{TH} + V_{BE} + (\beta + 1) I_B R_E$$

$$I_B R_{TH} + (\beta + 1) I_B R_E = V_{TH} - V_{BE}$$

$$I_B (R_{TH} + (\beta + 1) R_E) = V_{TH} - V_{BE}$$

$$\therefore I_B = \frac{V_{TH} - V_{BE}}{R_{TH} + (\beta + 1) R_E}$$

Assuming $\beta \gg 1$

$$\therefore I_B = \frac{V_{TH} - V_{BE}}{R_{TH} + \beta R_E}$$

$$I_C = \beta I_B$$

$$\therefore I_C = \frac{V_{TH} - V_{BE}}{\frac{R_{TH}}{\beta} + R_E} \asymp I_E \quad \dots (1)$$

~~(b) Output section~~

$$V_{CC} = V_{CE} + (R_C + R_E) I_C$$

$$\therefore V_{CE} = V_{CC} - (R_C + R_E) I_C \quad \dots (2)$$

$$I_C \approx I_E = \frac{V_{TH} - V_{BE}}{\frac{R_{TH}}{\beta} + R_E}$$

(B)

To make I_E independent of B

$$R_E \gg \frac{R_{TH}}{\beta}$$

In actual practice it is achieved by making R_E 10 times greater than $\frac{R_{TH}}{\beta}$

$$\therefore R_E \gg 10 \frac{R_{TH}}{\beta}$$

$$\text{or } R_{TH} \leq 0.1 \beta R_E$$

Usually $R_2 < R_1$

$$\therefore R_{TH} = R_1 // R_2 \approx R_2$$

$$\therefore \boxed{R_2 \leq 0.1 \beta R_E}$$

STABILITY FACTOR OF VOLTAGE DIVIDER BIAS.

$$V_{TH} = I_B R_{TH} + V_{BE} + I_E R_E$$

$$\text{putting } I_E = I_C + I_B$$

$$\therefore V_{TH} = I_B R_{TH} + V_{BE} + (I_C + I_B) R_E$$

$$V_{TH} = I_B R_{TH} + I_B R_E + V_{BE} + I_C R_E$$

$$\therefore I_B (R_{TH} + R_E) = V_{TH} - V_{BE} - I_C R_E$$

$$\therefore I_B = \frac{V_{TH} - V_{BE}}{R_E + R_{TH}} - \frac{I_C R_E}{R_E + R_{TH}}$$

Differentiating w.r.t. I_C ,

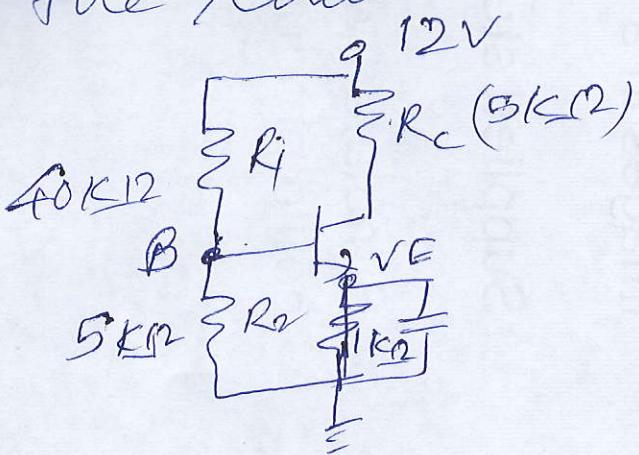
$$\therefore \frac{dI_B}{dI_C} = -\frac{R_E}{R_E + R_{TH}}$$

$$\therefore S = \frac{1+B}{1-B\frac{dI}{dR}} = \frac{1+B}{1+B \times \frac{R_E}{R_E+R_{TH}}} \quad (14)$$

$$= \frac{1+B}{1+\frac{B R_E}{R_E+R_{TH}}}$$

Problems on voltage divider bias

(i) Using approximate analysis, calculate the d.c. bias voltages & currents for the circuit. Assume $V_{BE} = 0.3V$ & $B = 60$



$$V_B = \frac{R_2}{R_1 + R_2} V_{CC} = \frac{5 \times 10^3}{(40 + 5) \times 10^3} \times 12$$

$$= 1.3V$$

$$I_E = \frac{V_B - V_{BE}}{R_E} = \frac{1.3 - 0.3}{1 \times 10^3} = 1mA$$

$$I_C \approx I_E = 1mA \quad \dots (1)$$

$$V_{CE} = V_{CC} - (R_C + R_E) I_C$$

$$= 12 - (5 + 1) \times 10^3 \times 10^{-3}$$

$$= 12 - 6 = 6V \quad (2)$$

(15)
Q) Solve problem Q using exact analysis
/Thevenin's theorem.

$$V_{TH} = \frac{R_2}{R_1 + R_2} \times V_{CC} = \frac{5 \times 10^3}{(40+5) \times 10^3} \times 12 \\ = 1.3 \text{ V}$$

$$R_{TH} = \frac{R_1 R_2}{R_1 + R_2} = \frac{40 \times 10^3 \times 5 \times 10^3}{(40+5) \times 10^3} \\ = 4.44 \text{ k}\Omega$$

$$I_B = \frac{V_{TH} - V_{BE}}{R_{TH} + R_E} = \frac{1.3 - 0.3}{4.44 \times 10^3 + 60 \times 10^3} \\ = 15.52 \text{ mA}$$

$$I_C = \beta I_B = 60 \times 15.52 \times 10^{-3} = 0.93 \text{ mA}$$

$$V_{CE} = V_{CC} - (R_E + R_C) I_C \\ = 6.42 \text{ V}$$

Assignment problems.

Calculate V_{CE} & I_C for the circuit

Given $R_1 = 40 \text{ k}\Omega$, $R_2 = 4 \text{ k}\Omega$, $R_E = 10 \text{ k}\Omega$

$R_C = 1.5 \text{ k}\Omega$, $V_{BE} = 0.5 \text{ V}$, $\beta = 40$ & $V_{CC} = 22 \text{ V}$

(1) Using approximate analysis

(2) Using exact analysis